★ Green Device Available
★ Super Low Gate Charge
★ Excellent Cdv/dt effect decline
★ Advanced high cell density Trench technology

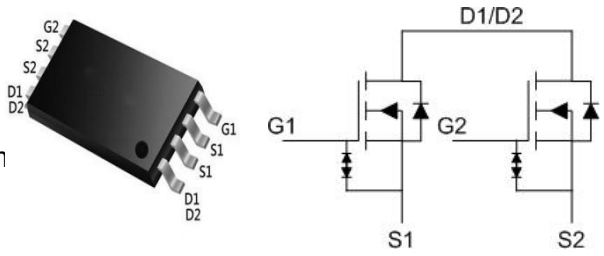
Product Summary

BVDSS	RDSON	ID
20V	9mΩ	7A

Description

The AO8810 is the low $R_{DS(ON)}$ trenched N- CH MOSFETs with robust ESD protection.
This product is suitable for Lithium-ion battery pack applications.
The AO8810 meet the RoHS and Green Product requirem with full function reliability approved.

TSSOP8 Pin Configuration



Product	Package	Marking	Packing	Min Unit Quantity
AO8810	TSSOP8	8810	3000PCS/Reel	3000PCS

Absolute Maximum Ratings (T_A=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		20	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current	T_A = 25℃	7	A
		T_A = 100℃	5	A
I_{DM}	Pulsed Drain Current note1		24	A
P_D	Power Dissipation	T_A = 25℃	1.53	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		111	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	20	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V , I_D=3.5A		9	13	mΩ
		V_{GS}=2.5V , I_D=3.5A		12.5	17	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	0.5	---	1.2	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=16V , V_{GS}=0V , T_J=25℃	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±8V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=3.5A	---	20	---	S
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=4.5V , I_D=7A	---	11.3	---	nC
Q_{gs}	Gate-Source Charge		---	1.89	---	
Q_{gd}	Gate-Drain Charge		---	3.56	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=10V , V_{GS}=4.5V , R_G=3.3Ω I_D=3.5A	---	8	---	ns
T_r	Rise Time		---	17	---	
$T_{d(off)}$	Turn-Off Delay Time		---	27	---	
T_f	Fall Time		---	8.8	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	955	---	pF
C_{oss}	Output Capacitance		---	200	---	
C_{rss}	Reverse Transfer Capacitance		---	150	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	7	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :
1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3. The power dissipation is limited by 150℃ junction temperature
4. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

ypical Performance Characteristics

Figure1: Output Characteristics

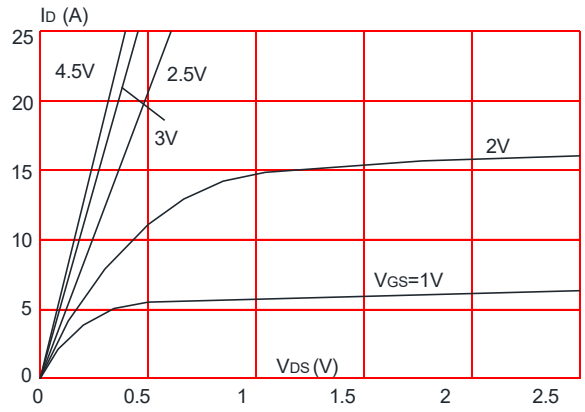


Figure 2: Typical Transfer Characteristics

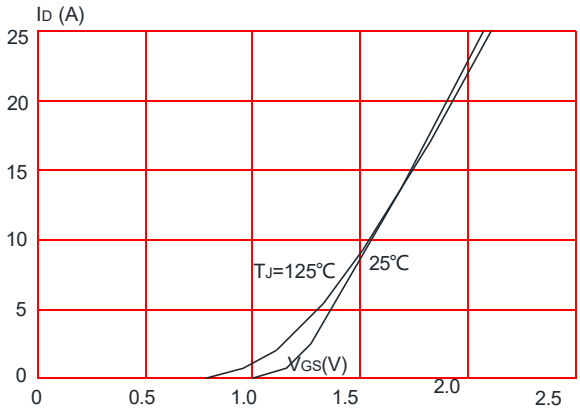


Figure 3: On-resistance vs. Drain Current

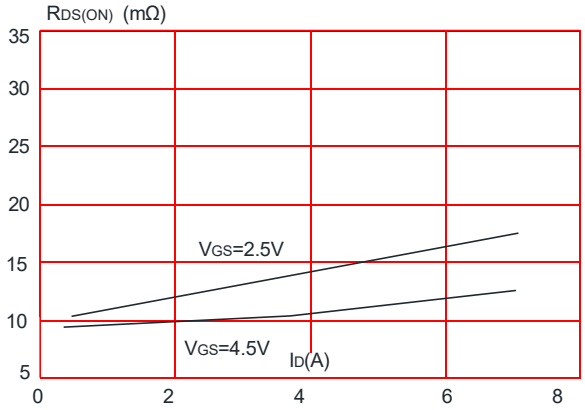


Figure 4: Body Diode Characteristics

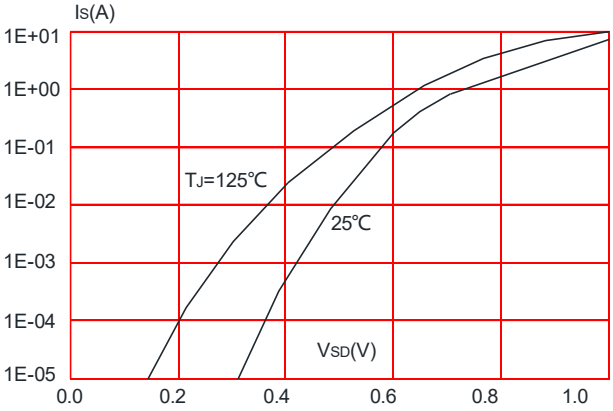


Figure 5: Gate Charge Characteristics

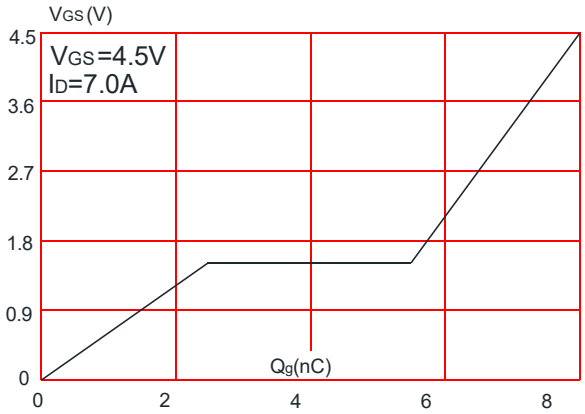


Figure 6: Capacitance Characteristics

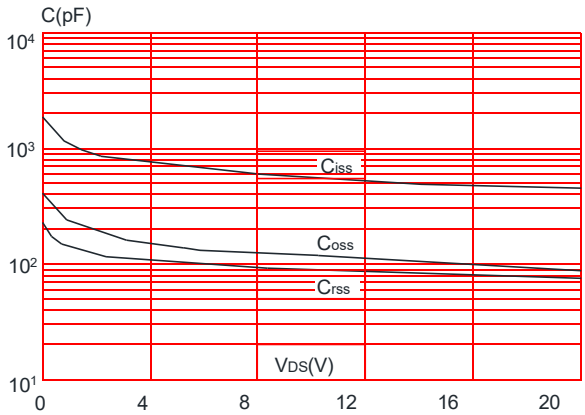


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

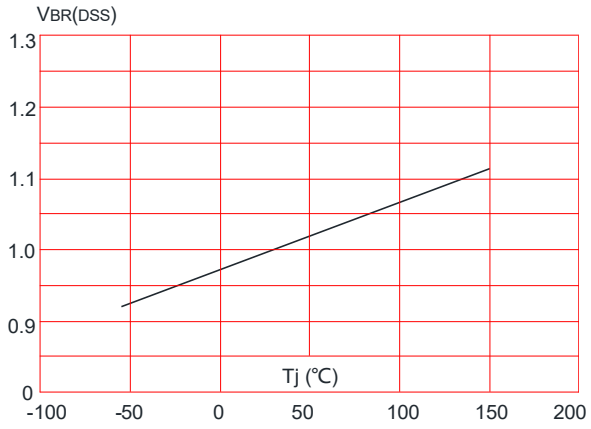


Figure 8: Normalized on Resistance vs. Junction Temperature

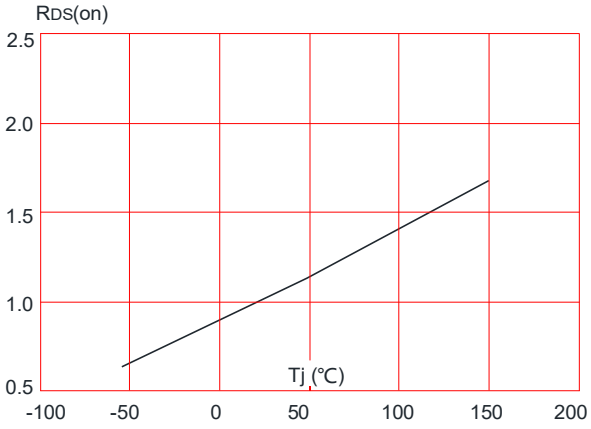


Figure 9: Maximum Safe Operating Area

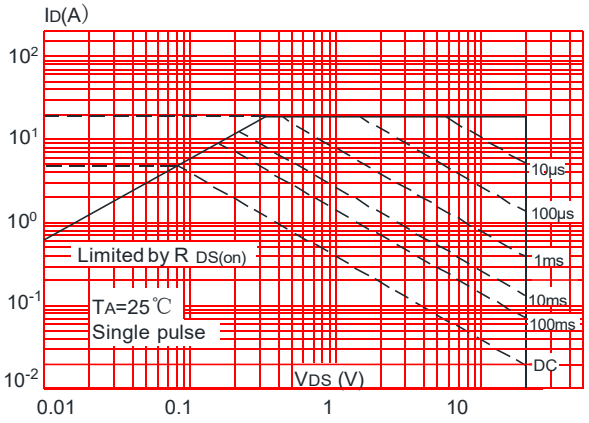


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

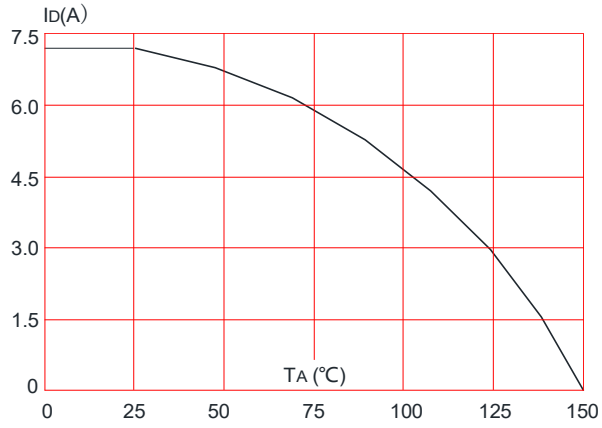
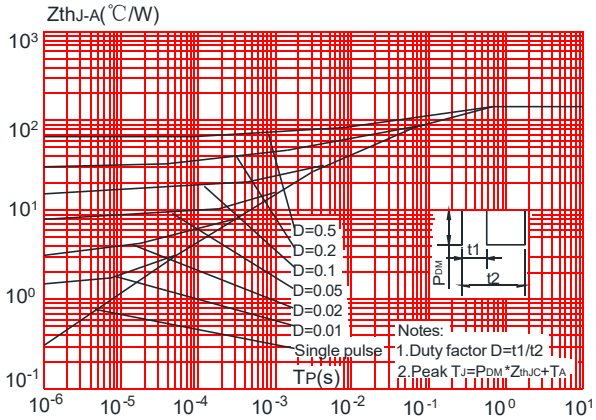
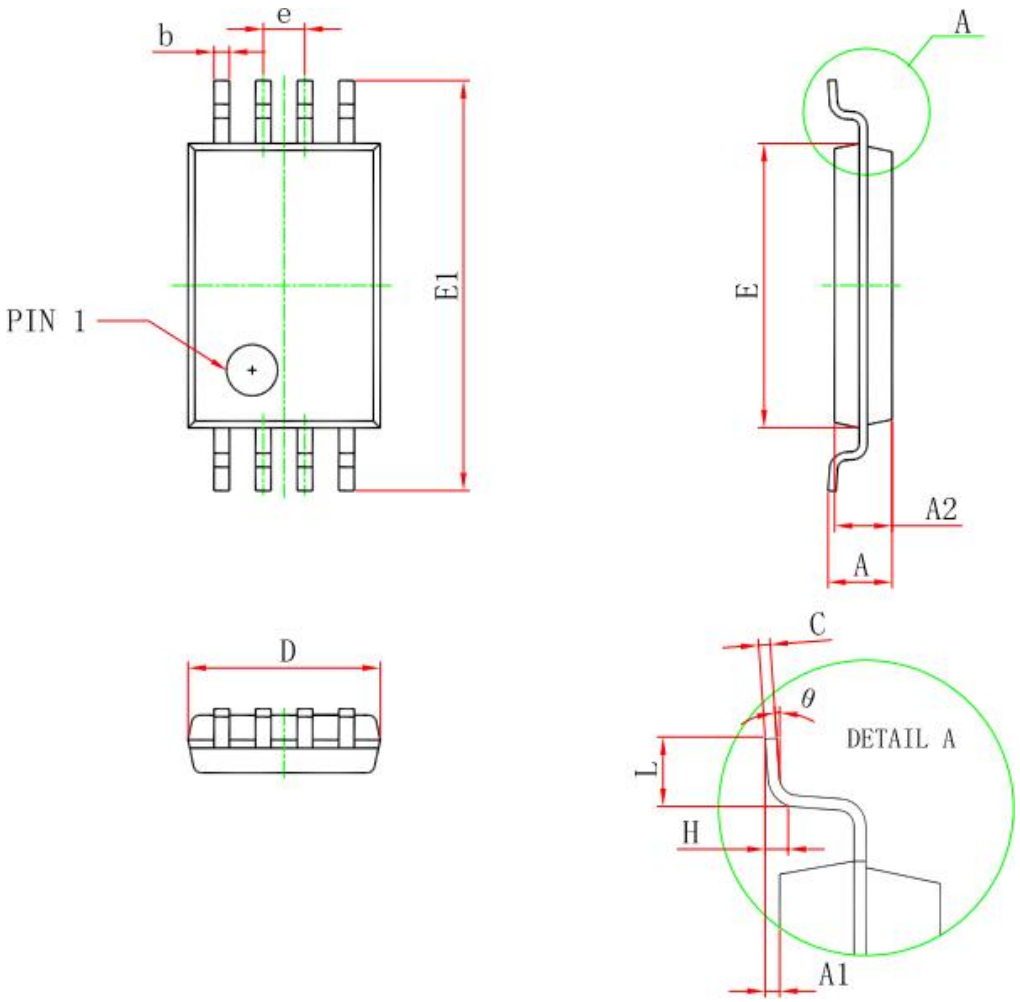


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



TSSOP8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.200		0.047
A2	0.800	1.000	0.031	0.039
A1	0.050	0.150	0.002	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028
H	0.25(TYP)		0.01(TYP)	
θ	1°	7°	1°	7°